

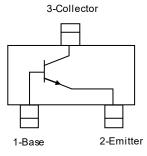
## PNT523T503E0-2

## High EB High DC gain Ultra-Small package switch transistor

#### Feature

This device is Pb-Free, Halogen Free/BFR Free and RoHS compliant.

- Package: SOT-523
- Emitter -Base Breakdown Voltage 11V
- > High DC current gain typical 380
- Low Saturation Voltage 80mv
- > 0.15 continuous collector current
- NPN switch transistor



#### Top View

#### **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260 °C
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- ➢ Pin flatness :≤3mil

## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Value	Units
Collector-Emitter Breakdown Voltage	V (BR)CEO	50	V
Collector-Base Breakdown Voltage	V (BR)CBO	80	V
Emitter -Base Breakdown Voltage	V (BR)EBO	11	V
Collector Current	lc	0.15	А
Total Dissipation @25°C	P <sub>tot</sub>	0.15	W
Storage Temperature	T <sub>stg</sub>	-65~150	°C
Max. Operating Junction Temperature	Tj	150	°C

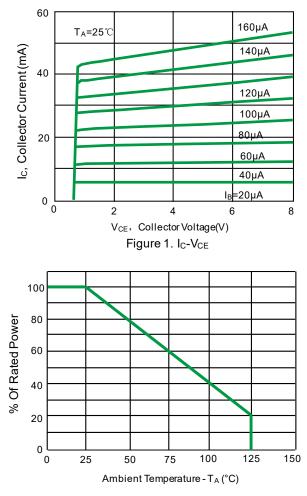
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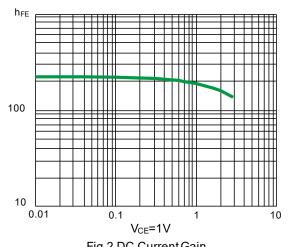
### Absolute maximum rating@25℃

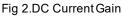
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =50uA	80			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =1mA	50			V
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =50uA		11		V
Collector Cut-off Current (I <sub>E</sub> =0)	I <sub>CBO</sub>	V <sub>CB</sub> =60V			0.1	μA
Emitter Cut-off Current(Ic=0)	I <sub>EBO</sub>	V <sub>EB</sub> =7V			0.1	μA
DC Current Gain	h <sub>FE</sub>	I <sub>C</sub> =1mA,V <sub>CE</sub> =6V	200		350	-
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	I <sub>C</sub> =50mA,I <sub>B</sub> =5mA	-	0.08		V
Transition frequency	f⊤	V <sub>CE</sub> =12V,I <sub>E</sub> =-2mA,f=100MHz		200		MHz
Output Capacitance	Cob	V <sub>CE</sub> =12V,I <sub>E</sub> =0mA,f=1MHz		2	3.5	pF

## **Typical Characteristics**









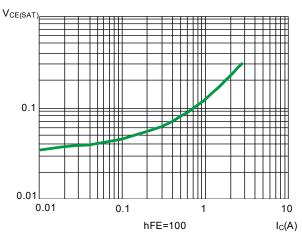
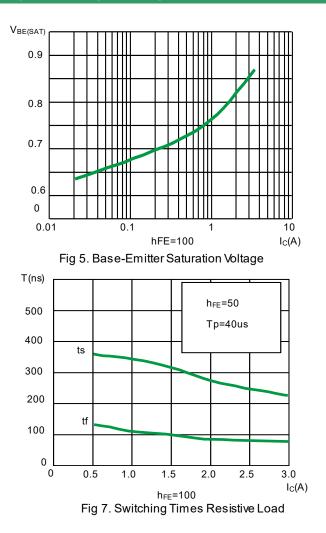


Fig 4.Collector-Emitter Saturation Voltage

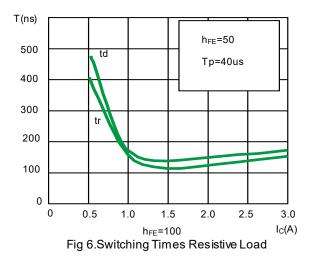
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#### **Solder Reflow Recommendation**

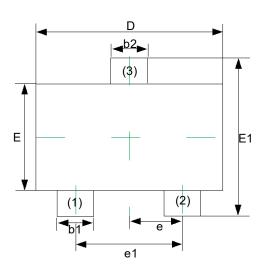
Time (sec)

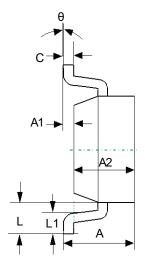
Peak Temp=257 °C, Ramp Rate=0.802deg. °C/sec



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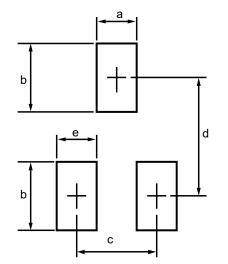
# Product dimension (SOT-523)





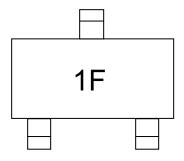
Dim	Millim	eters	Inches		
Dilli	MIN	МАХ	MIN	МАХ	
Α	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
с	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500TYP		0.020TYP		
e1	0.900	1.100	0.035	0.043	
L	0.400REF		0.016REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

# High EB High DC gain Ultra-Small package switch transistor PNT523T503E0-2



Dim	Millimeters			
	MIN	МАХ		
а		0.5		
b	-	0.6		
с	-	1.0		
d	-	1.24		
е	-	0.4		

# Marking information



## **Ordering information**

Device	Package	Reel	Shipping
PNT523T503E0-2	SOT-523 (Pb-Free)	7"	3000 / Tape & Reel

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